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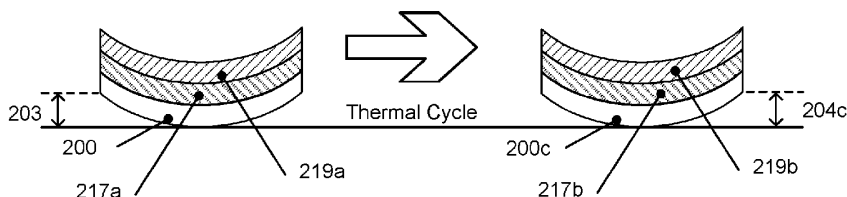


FIG. 2C

(57) Abstract: Mitigating wafer bow of a semiconductor wafer includes depositing one or more backside layers that compensate for wafer bow caused by one or more frontside layers. Deposition of a backside layer stack may mitigate wafer bow before and after annealing without changing the magnitude of the wafer bow compensated by the backside layer stack. Each of the backside layers may be deposited by a backside deposition apparatus.

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